TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPCA8053-H**

Switching Regulator Applications Motor Drive Applications DC-DC Converter Applications

- Small footprint due to a small and thin package
- · High-speed switching
- Small gate charge: Q<sub>SW</sub> = 6.9 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS (ON)} = 13.9 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: |Yfs| = 46 S (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.2 mA)

### Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	60	V	
Drain-gate voltage (R	GS = 20 kΩ)	$V_{DGR}$	60	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	ID	15	Α	
Drain current	Pulsed (Note 1)	$I_{DP}$	45 30	, \	
Drain power dissipati	on (Tc = 25°C)	$P_{D}$	30	W	
Drain power dissipati	on (t = 10 s) (Note 2a)	$P_{D}$	2.8	W	
Drain power dissipati	on (t = 10 s) (Note 2b)	P <sub>D</sub>	1.6	W	
Single-pulse avalance	ne energy (Note 3)	E <sub>AS</sub>	16	mJ	
Avalanche current		I <sub>AR</sub>	15	Α	
Repetitive avalanche (To	energy c = 25°C) (Note 4)	E <sub>AR</sub>	1.53	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

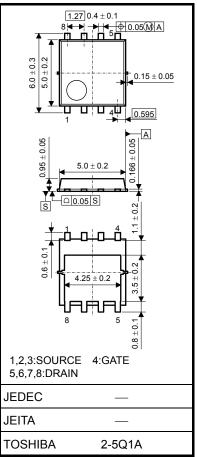
Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

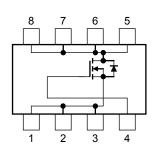
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.069 g (typ.)

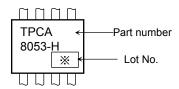
### **Circuit Configuration**



#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R <sub>th (ch-c)</sub>	4.17	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

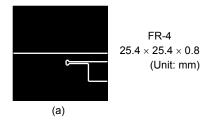
## Marking (Note 5)

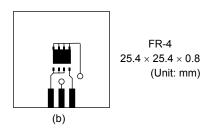


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

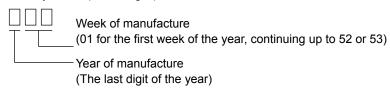




Note 3:  $V_{DD}$  = 24 V,  $T_{ch}$  = 25°C (initial), L = 100  $\mu$ H,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 15 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



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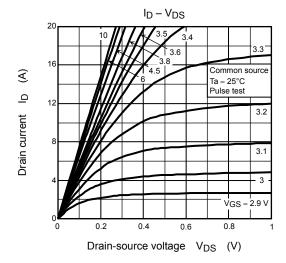
## **Electrical Characteristics (Ta = 25°C)**

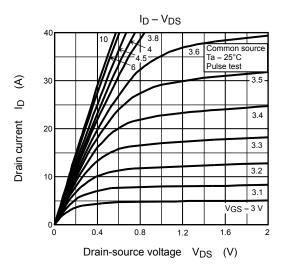
Ch	Characteristic		Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	nt	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V		_	10	μА
Drain agurag bro	akdowa voltago	V <sub>(BR)DSS</sub>	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	—     —     10       60     —     —       43     —     —       1.3     —     2.3       —     15.6     24.0       —     13.9     22.3       23     46     —       —     1620     2110       —     60     90       —     200     —       —     2.3     3.5       —     2.4     —       —     9.1     —       —     7.0     —       —     33     —	V		
Dialii-source brea	akdown voltage	V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	43	_	_	v
Gate threshold vo	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA}$	1.3	_	2.3	V
Drain accurac ON resistance		Pro (ON)	$V_{GS} = 4.5 \text{ V}, I_D = 7.5 \text{ A}$		15.6	24.0	mΩ
Dialii-source Oiv	-iesistance	NDS (ON)	$V_{GS} = 10 \text{ V}, I_D = 7.5 \text{ A}$	—       —       ±100         —       —       10         60       —       —         43       —       —         1.3       —       2.3         —       15.6       24.0         —       13.9       22.3         23       46       —         —       60       90         —       200       —         —       2.3       3.5         —       2.4       —         —       9.1       —         —       9.1       —         —       7.0       —         —       33       —         —       25       —         —       13       —         —       5.5       —	11152		
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_D = 7.5 \text{ A}$	23	46	_	S
Input capacitance	)	C <sub>iss</sub>		_	1620	2110	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	60	90	pF
Output capacitance		C <sub>oss</sub>		_	200	_	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$	_	2.3	3.5	Ω
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Rise time	t <sub>r</sub>	10 V 🔲 In = 7.5 A	_	2.4	_	
	_						
Switching time	Fall time	t <sub>f</sub>	R = 4.7 D	_	7.0	15.6     24.0       13.9     22.3       46     —       1620     2110       60     90       200     —       2.3     3.5       2.4     —       9.1     —       7.0     —       33     —       25     —       13     —       5.5     —	ns
	Turn-off time	t <sub>off</sub>		_	33	_	
Total gate charge	;	V <sub>DD</sub> ≈ 48 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A — 25 —		_			
(gate-source plus	gate-drain)	Qg	$V_{DD} \approx 48 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 15 \text{ A}$		13	_	
Gate-source charge 1		Q <sub>gs1</sub>		_	5.5	_	nC
-		Q <sub>gd</sub>	$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	_	4.4	_	
Gate switch charg	ge	Q <sub>SW</sub>		_	6.9	_	

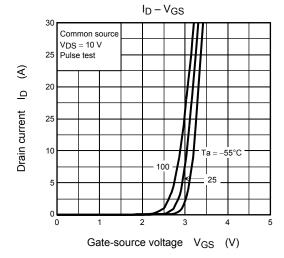
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

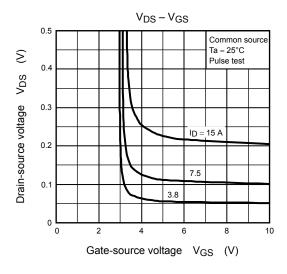
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	45	Α
Forward voltage (diode)			$V_{DSF}$	$I_{DR} = 15 \text{ A}, V_{GS} = 0 \text{ V}$	_		-1.2	V

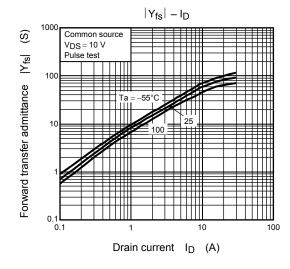
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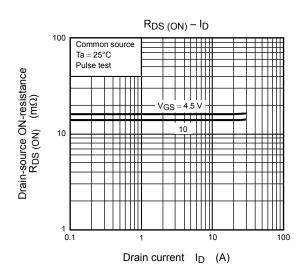


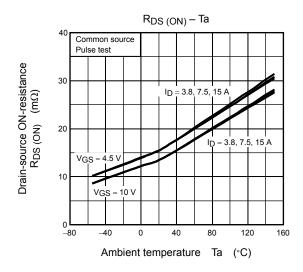


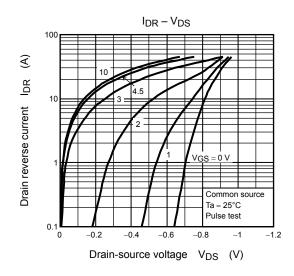


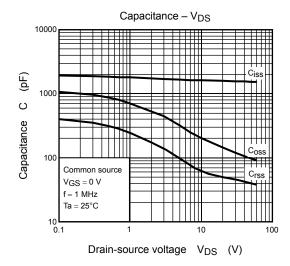


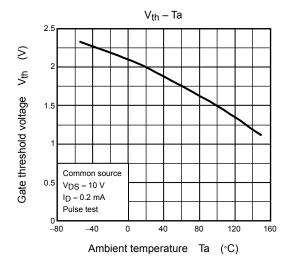


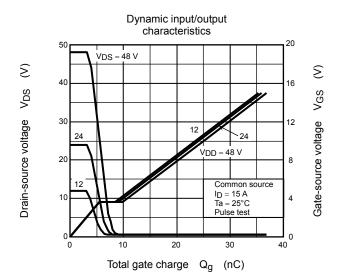




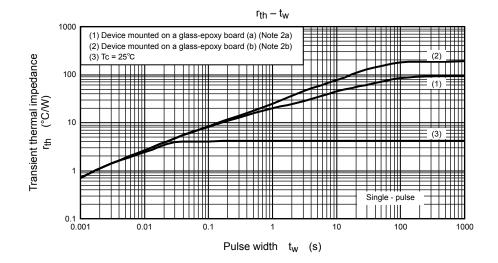


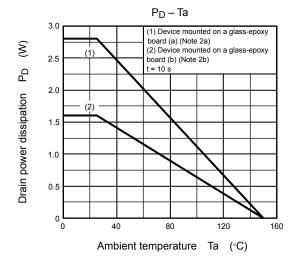


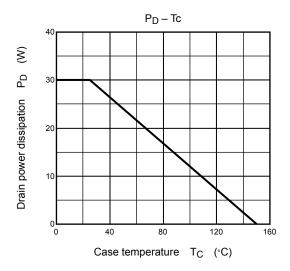


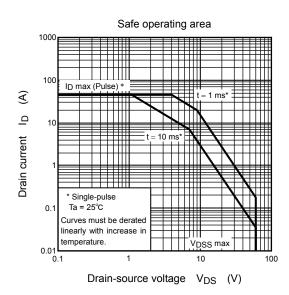


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